









SN74HCS541 JAJSN30B – OCTOBER 2021 – REVISED OCTOBER 2022

SN74HCS541 シュミット・トリガ入力、3 ステート出力、フロースルー・ピン配置、オクタル・バッファ / ライン・ドライバ

1 特長

- 広い動作電圧範囲:2V~6V
- シュミット・トリガ入力により低速の信号またはノイズの多い信号に対応
- 低消費電力
 - I_{CC}: 100nA (標準値)
 - 入力リーク電流:±100nA (標準値)
- 6V で±7.8mA の出力駆動能力
- 拡張周囲温度範囲:-40℃~+125℃、TA

2 アプリケーション

- デジタル信号のイネーブルまたはディスエーブル
- 低速またはノイズの多い入力信号の除去
- コントローラ・リセット時の信号保持
- スイッチのデバウンス

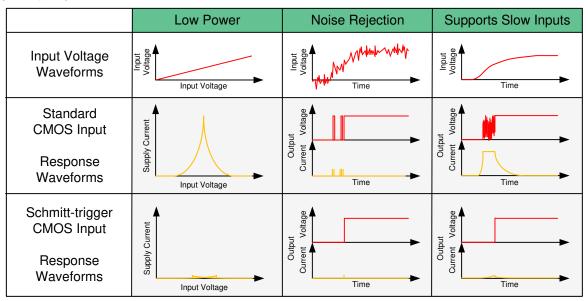
3 概要

SN74HCS541 は 3 ステート出力とシュミット・トリガ入力を備えた 8 個のバッファを搭載しています。 アクティブ Low の出力イネーブル・ピン (OE1、OE2) は 8 つのチャネルをすべて制御し、この両方が Low のときのみ出力がアクティブになるよう構成されています。

パッケージ情報

部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)			
SN74HCS541	RKS (VQFN, 20)	4.50mm × 2.50mm			
SN/4HCS541	DGS (SOT, 20)	5.10mm × 3.00mm			

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



シュミット・トリガ入力の利点



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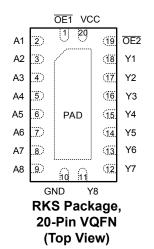
4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision A (August 2022) to Revision B (October 2022)				
ウェッタブル・フランクを削除	1			
Added DGS (SOT) package to Pin Configuration				
Added DGS (SOT) package to Thermal Information				
Changes from Revision * (October 2021) to Revision A (August 2022)	Page			
Updated the Example Layout for the SN74HCS541 in the RKS Package figure	14			



5 Pin Configuration and Functions



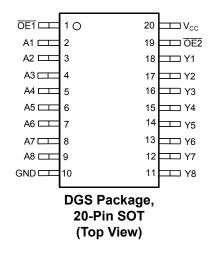


表 5-1. Pin Functions

PIN NAME NO.		TYPE ⁽¹⁾	DESCRIPTION	
		ITPE	DESCRIPTION	
OE1	1	I	Output enable input 1, active low	
A1	2	I	Input for channel 1	
A2	3	I	Input for channel 2	
A3	4	I	Input for channel 3	
A4	5	I	Input for channel 4	
A5	6	I	Input for channel 5	
A6	7	I	Input for channel 6	
A7	8	1	Input for channel 7	
A8	9	I	Input for channel 8	
GND	10	G	Ground	
Y8	11	0	Output for channel 8	
Y7	12	0	Output for channel 7	
Y6	13	0	Output for channel 6	
Y5	14	0	Output for channel 5	
Y4	15	0	Output for channel 4	
Y3	16	0	Output for channel 3	
Y2	17	0	Output for channel 2	
Y1	18	0	Output for channel 1	
ŌE2	19	I	Output enable input 2, active low	
V _{CC}	20	Р	Positive supply	
I nermai Pan(²/ — — —		_	The thermal pad can be connect to GND or left floating. Do not connect to any other signal or supply.	

⁽¹⁾ I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

⁽²⁾ RKS package only.



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC+0.5} \text{ V}$		±20	mA
Io	Continuous output current	$V_O = 0$ to V_{CC}		±35	mA
I _{CC}	Continuous current through V _{CC} or C	GND		±70	mA
TJ	Junction temperature ⁽³⁾			150	°C
T _{stg}	Storage temperature		-65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Guaranteed by design.

6.2 ESD Ratings

				VALUE	UNIT
			Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	
V _(ESD))	Electrostatic discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2	5	6	V
VI	Input voltage	0		V _{CC}	V
Vo	Output voltage	0		V _{CC}	V
T _A	Ambient temperature	-40		125	°C

6.4 Thermal Information

		SN74F		
THERMAL METRIC(1)		RKS (VQFN)	DGS (SOT)	UNIT
		20 PINS	20 PINS	-
R _{0JA}	Junction-to-ambient thermal resistance	83.2	130.6	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	82.6	68.7	°C/W
R _{0JB}	Junction-to-board thermal resistance	57.4	85.4	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	14.5	10.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	56.4	85.0	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	40.0	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: SN74HCS541

6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

	PARAMETER	TEST CO	NDITIONS	V _{cc}	MIN	TYP	MAX	UNIT
				2 V	0.7		1.5	
V _{T+}	Positive switching threshold			4.5 V	1.7		3.15	V
				6 V	2.1		4.2	
				2 V	0.3		1	
V _{T-}	Negative switching threshold			4.5 V	0.9		2.2	V
				6 V	1.2		3	
				2 V	0.2		1	
ΔV_T	Hysteresis (V _{T+} - V _{T-})			4.5 V	0.4		1.4	V
				6 V	0.6		1.6	
			I _{OH} = -20 μA	2 V to 6 V	V _{CC} - 0.1	V _{CC} - 0.002		
V _{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OH} = -6 \text{ mA}$	4.5 V	4	4.3		V
			$I_{OH} = -7.8 \text{ mA}$	6 V	5.4	5.75		
			I _{OL} = 20 μA	2 V to 6 V		0.002	0.1	
V _{OL}	Low-level output voltage	$V_I = V_{IH}$ or V_{IL}	I _{OL} = 6 mA	4.5 V		0.18	0.3	V
			I _{OL} = 7.8 mA	6 V		0.22	0.33	
I _I	Input leakage current	$V_I = V_{CC}$ or 0		6 V		±100	±1000	nA
l _{oz}	Off-state (high-impedance state) output current	$V_O = V_{CC}$ or 0		6 V		±0.01	±2	μA
I _{CC}	Supply current	$V_I = V_{CC}$ or 0, I_C) = 0	6 V		0.1	2	μA
Ci	Input capacitance			2 V to 6 V			5	pF

6.6 Switching Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurment Information*. C_L = 50 pF.

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	Vcc	MIN	TYP	MAX	UNIT			
				2 V		13	45				
t _{pd}	Propagation delay	Α	Y	4.5 V		7	18	ns			
				6 V		6	16				
				2 V		15	44				
t _{en}	Enable time	e time OE Y	ŌĒ	ŌĒ	OE Y	Y	4.5 V		7	22	ns
				6 V		6	18				
		2 V		2 V		12	30				
t _{dis}	Disable time		ŌĒ	ŌĒ	ŌĒ	Y	4.5 V		9	20	ns
			6 V		8	19					
				2 V		9	16				
t _t	Transition-time		Any	4.5 V		5	9	ns			
				6 V		4	8				

6.7 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{pd}	Power dissipation capacitance per gate	No load		20		pF

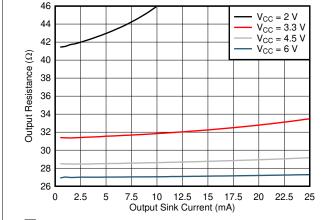
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6.8 Typical Characteristics

 $T_A = 25^{\circ}C$



☑ 6-1. Output Driver Resistance in LOW State

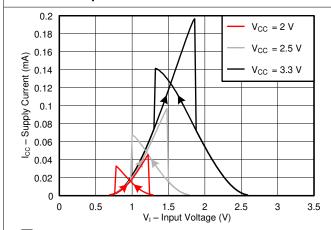


図 6-3. Supply Current Across Input Voltage, 2-, 2.5-, and 3.3-V Supply

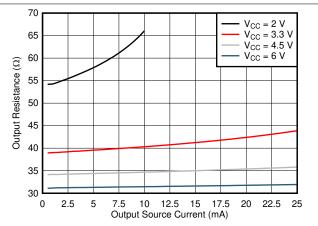


図 6-2. Output Driver Resistance in HIGH State

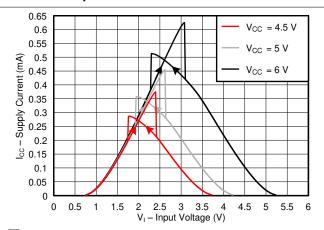


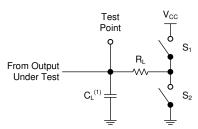
図 6-4. Supply Current Across Input Voltage, 4.5-, 5-, and 6-V Supply

7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_t < 2.5 ns.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) C_L includes probe and test-fixture capacitance.

図 7-1. Load Circuit for 3-State Outputs

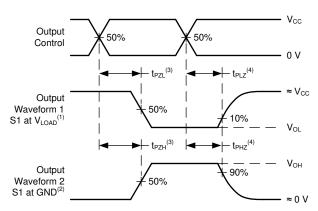
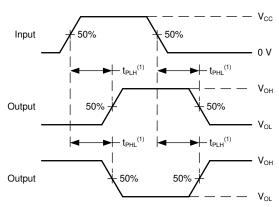
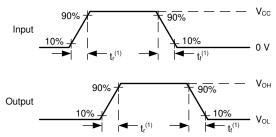


図 7-3. Voltage Waveforms Propagation Delays



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

図 7-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

図 7-4. Voltage Waveforms, Input and Output Transition Times

8 Detailed Description

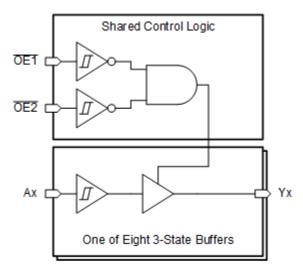
8.1 Overview

The SN74HCS541 contains eight buffers with 3-state outputs and Schmitt-trigger inputs. The active low output enable pins ($\overline{OE1}$ and $\overline{OE2}$) control all eight channels, and are configured so that both must be low for the outputs to be active.

When the outputs are enabled, the outputs are actively driving low or high.

When the outputs are disabled, the outputs are set into the high-impedance state.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a $10-k\Omega$ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.3 Open-Drain CMOS Outputs

This device includes open-drain CMOS outputs. Open-drain outputs can only drive the output low. When in the high logical state, open-drain outputs will be in a high-impedance state. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10 k Ω resistor can be used to meet these requirements.

Unused open-drain CMOS outputs should be left disconnected.

8.3.4 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law $(R = V \div I)$.

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see *Understanding Schmitt Triggers*.

8.3.5 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law $(R = V \div I)$.

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the *Implications of Slow or Floating CMOS Inputs* application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-k Ω resistor is recommended and will typically meet all requirements.

8.3.6 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law $(R = V \div I)$.

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a $10-k\Omega$ resistor, however, is recommended and will typically meet all requirements.

8.3.7 Clamp Diode Structure

As shown in 🗵 8-1, the inputs and outputs to this device have both positive and negative clamping diodes.

注意

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

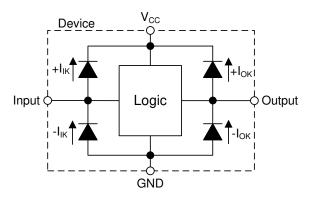


図 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

表 8-1. Function Table

	OUTPUT ⁽²⁾		
OE1	OE2	Α	Y
L	L	L	L
L	L	Н	Н
Н	X	Х	Z
Х	Н	Х	Z

- (1) L = input low, H = input high, X = do not care
- (2) L = output low, H = output high, Z = high impedance

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9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74HCS541 can be used to drive signals over relatively long traces or transmission lines. In order to reduce ringing caused by impedance mismatches between the driver, transmission line, and receiver, a series damping resistor placed in series with the transmitter's output can be used. The figure in the *Application Curve* section shows the received signal with three separate resistor values. Just a small amount of resistance can make a significant impact on signal integrity in this type of application.

9.2 Typical Application

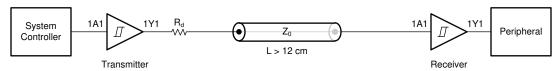


図 9-1. Typical Application Block Diagram

9.2.1 Design Requirements

- All signals in the system operate at 5 V
- Avoid unstable state by not having LOW signals on both inputs
- Q output is HIGH when S̄ is LOW
 - Q output remains HIGH until R is LOW

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS541 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS541 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCS541 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74HCS541 can drive a load with total resistance described by $R_L \ge V_O$ / I_O , with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.



Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear* and Logic (SLL) Packages and Devices.

注意

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74HCS541 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74HCS541 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the
 device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the Layout
 section.
- 2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS541 to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in M Ω ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

9.2.3 Application Curves

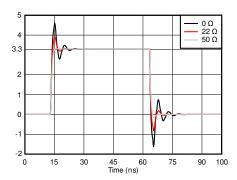


図 9-2. Simulated Signal Integrity at the Receiver With Different Damping Resistor (R_d) Values

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in the following layout example.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.



11.2 Layout Example

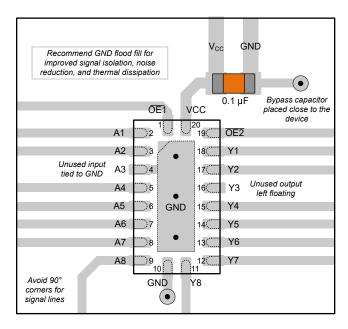


図 11-1. Example Layout for the SN74HCS541 in the RKS Package

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, HCMOS Design Considerations application report
- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report
- Texas Instruments, Designing With Logic application report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 サポート・リソース

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
SN74HCS541DGSR	Active	Production	VSSOP (DGS) 20	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HS541
SN74HCS541DGSR.A	Active	Production	VSSOP (DGS) 20	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HS541
SN74HCS541RKSR	Active	Production	VQFN (RKS) 20	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS541
SN74HCS541RKSR.A	Active	Production	VQFN (RKS) 20	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS541
SN74HCS541RKSRG4	Active	Production	VQFN (RKS) 20	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS541
SN74HCS541RKSRG4.A	Active	Production	VQFN (RKS) 20	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS541

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF SN74HCS541:

Automotive: SN74HCS541-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS541DGSR	VSSOP	DGS	20	5000	330.0	16.4	5.4	5.4	1.45	8.0	16.0	Q1
SN74HCS541RKSR	VQFN	RKS	20	3000	180.0	12.4	2.8	4.8	1.2	4.0	12.0	Q1
SN74HCS541RKSRG4	VQFN	RKS	20	3000	180.0	12.4	2.8	4.8	1.2	4.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS541DGSR	VSSOP	DGS	20	5000	353.0	353.0	32.0
SN74HCS541RKSR	VQFN	RKS	20	3000	210.0	185.0	35.0
SN74HCS541RKSRG4	VQFN	RKS	20	3000	210.0	185.0	35.0

2.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC QUAD FLATPACK - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



PLASTIC QUAD FLATPACK - NO LEAD



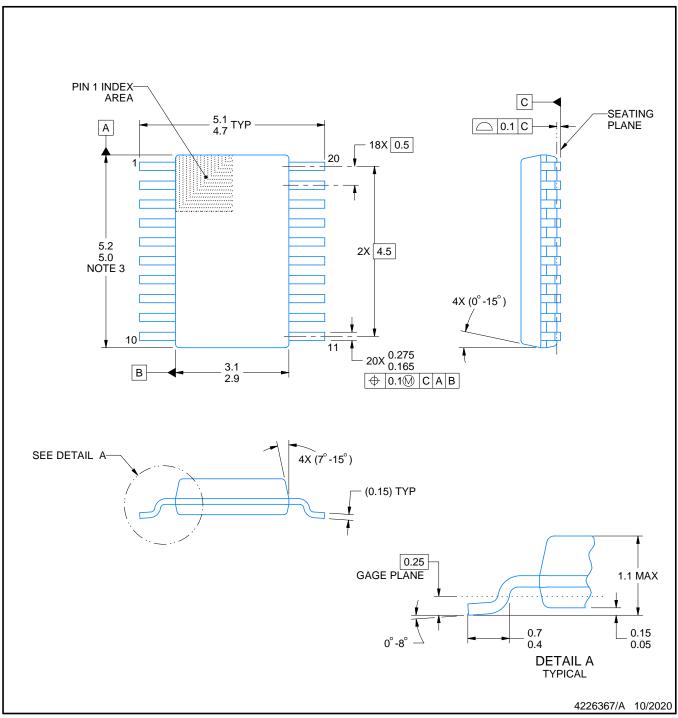
NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

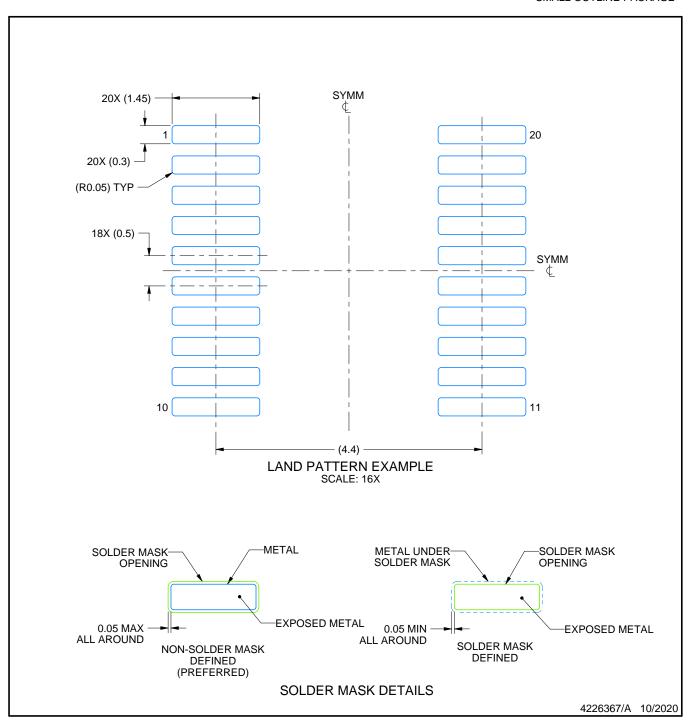
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. No JEDEC registration as of September 2020.
- 5. Features may differ or may not be present.



SMALL OUTLINE PACKAGE

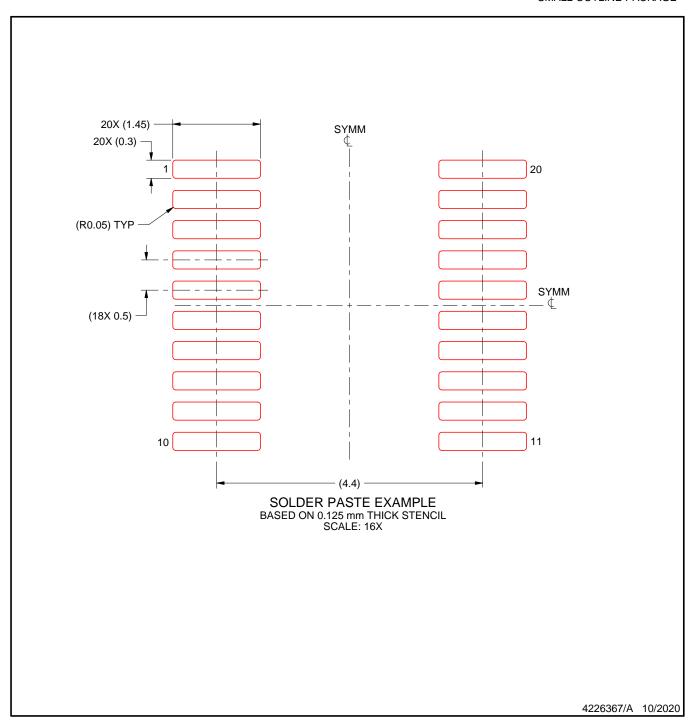


NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
- 9. Size of metal pad may vary due to creepage requirement.
- Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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